

Amendments to the Specification

Please amend the Paragraphs [0006] and [00018] in the Publication of the subject application (20060099422 A1 published May 11, 2006) as noted below. The undersigned brings to the Examiner's attention that the originally filed English translation of the specification is correct.

[0006] In DE 195 22 371 it is proposed for the applying of a diamond layer to a hard metal substrate a first Co-selective etching step with subsequent cleaning of the etched substrate surface and then a WC-selective etching step with subsequent cleaning. To the hard metal substrate ~~pr-treated~~ pre-treated in this manner is applied a diamond layer by means of a CVD process.

[0018] In accordance with a further embodiment of the invention there is disposed a porous zone between the first region and the diamond layer in which the hard material particles ~~ae~~ are free of binding material. The hard material particle structure is preferably intact in the porous zone and not weakened by etching at the grain boundaries. The porous zone is followed by the diamond layer above. A better layer adhesion is obtained due to the removing of the binding material in the porous zone.